

## R-C Thermal Model Parameters

### DESCRIPTION

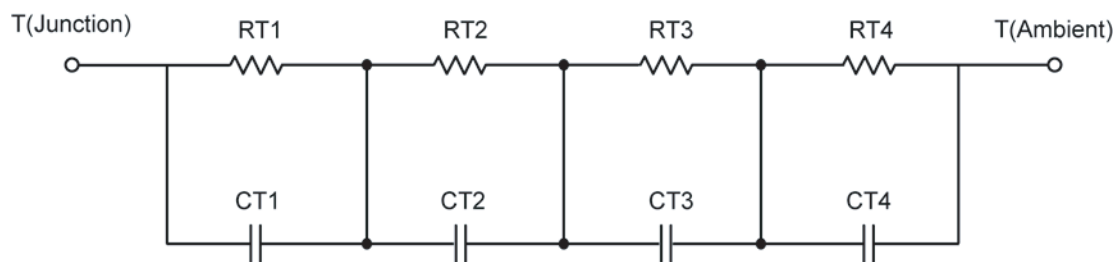
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	54.1717	N/A	48.0707
RT2	16.1135	N/A	12.9024
RT3	71.7294	N/A	8.5961
RT4	77.9854	N/A	30.4308
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.3525	N/A	592.9211 u
CT2	43.9187 u	N/A	49.6255 u
CT3	8.9982 m	N/A	265.2869 m
CT4	616.3284 u	N/A	2.9450 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	19.4916	N/A	15.2036
RF2	84.5646	N/A	70.0930
RF3	62.3054	N/A	274.2000 m
RF4	53.6384	N/A	14.4292
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	47.7227 u	N/A	41.4000 u
CF2	539.9065 u	N/A	488.7300 u
CF3	9.3099 m	N/A	27.9274 m
CF4	1.3482	N/A	26.8167 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

